

## INCHANGE SEMICONDUCTOR

## **isc** Silicon NPN Power Transistor

## BUX98A

### DESCRIPTION

- · High Voltage Capability
- · High Current Capability
- Fast Switching Speed
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

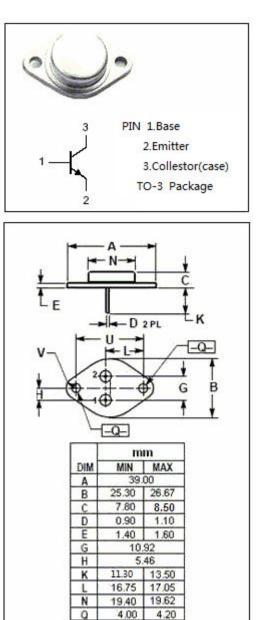
- High frequency and efficiency converters
- · Linear and switching industrial equipment

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1000	V
VCEO	Collector-Emitter Voltage	450	V
VEBO	Emitter-Base Voltage	7	V
lc	Collector Current-Continuous	30	А
I <sub>CM</sub>	Collector Current-peak ( tp <5 ms )	60	А
I <sub>B</sub>	Base Current-Continuous	8	А
I <sub>BM</sub>	Base Current-peak ( tp <5 ms )	30	А
Pc	Collector Power Dissipation $@T_c=25^{\circ}C$	250	W
Tj	Junction Temperature 2		°C
T <sub>stg</sub>	Storage Temperature Range	-65~200	°C

#### **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.7	°C/W



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30.20

4.50

30.00

4.30



## isc Silicon NPN Power Transistor

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## ELECTRICAL CHARACTERISTICS

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
⇔Vceo(sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	450			V
V <sub>CER(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>c</sub> = 1mA	1000			V
☆V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 16A ;I <sub>B</sub> = 3.2A			1.5	V
☆Vc∈(sat)-2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 24A ;I <sub>B</sub> = 5A			5.0	V
☆V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	Ic= 16A ;I <sub>B</sub> = 3.2A			1.6	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> =1000V; I <sub>E</sub> = 0 V <sub>CB</sub> =1000V; I <sub>E</sub> = 0 T <sub>C</sub> =125℃			0.4 4	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 450V; I <sub>B</sub> = 0			2	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			2	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	15		50	

 $\precsim$  Pulsed: Pulse duration = 300 ms, duty cycle = 1.5 %

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